

substance: boron compounds with group IV elements
property: properties of boron-zirconium compounds

ZrB

critical temperature of superconductivity

T_c	3.4 K	91F, 53H
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Band structure of Ti, Zr, Hf monoborides [89I].

ZrB₂

Metallic; preparation [75S, 52P, 77G1, 77L], crystalline structure [75S, 77G1], electronic structure [77G1, 77G2, 77P, 76G], electrical conductivity [79L], electrical transport [77C].

Some properties of ultrafine zirconium boride powders and films [93A].

Preparation of ultrafine zirconium boride powders and films [94A1].

Preparation and some properties of ultrafine ZrB₂ (and TiB₂) powders [95A].

Preparation by borothermic reduction (mechanochemical treatment) of zirconia [96M].

Preparation of high-purity ZrB₂ powder [95Z].

Growth and crystal data for preparation by high temperature solution growth [84L] and references therein.

Preparation of single crystals by the floating zone method [96O].

Interaction in ZrN-ZrB₂ and HfN-HfB₂ systems (X-ray diffraction, metallography, microhardness, melting point) [84O].

For structure and Brillouin zone see TiB₂, Fig. 1 and Fig. 2, respectively.

Space group: P6/mmm

lattice parameters

(in nm)

a	0.3170	86I
c	0.3531	
a	0.599	91S
c	0.671	

The cited papers don't give hints why the lattice parameters are so different.

interatomic distances

(in nm)

d	0.317(6)	Zr – Zr	91S
	0.183(3)	B – B	
	2.54(12)	Zr – B	

activation energy of chemical reaction

E_A	144.5(15) kJ mol ⁻¹	$T = 2609...2909$ K	from profile of combustion synthesis	92D
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electronic properties

Total and component electronic density of states calculation in Fig. 3 [91S].

resistivity

ρ	30 nΩ m	86I
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Hall coefficient

R_H	$-2.0 \cdot 10^{-3} \mu\text{m}^3\text{C}^{-1}$	86I
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carrier concentration

n	0.04 electrons / unit cell	91T
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carrier mobility

μ_H	$6.66 \cdot 10^{-2} \text{m}^2\text{V}^{-1} \text{s}^{-1}$	86I
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coeff. of electronic heat capacity

γ	$0.93 \text{mJ K}^{-2}\text{mol}^{-1}$	69T, 91T
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thermal diffusivity

D	$2.10 \cdot 10^{-3} \dots 1.79 \cdot 10^{-3} \quad T = 2609 \dots 2909 \text{ K}$ (units are missing)	92D
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thermal diffusivity of the reactants
in combustion synthesis

Properties of ultrafine ZrB₂ powders and films in [94A2].

Oxidation behavior of ZrB₂ [87K].

Oxidation behavior of ZrB₂ composite ceramics [87S].

ZrB₁₂

Superconducting; preparation [75S], crystalline structure [75S], Curie temperature [71F], magnetic properties [73O]

critical temperature of superconductivity

T_c	6.03 K	91F, 68M
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ZrB₅₁

Interstitally doped β-rhombohedral boron, see LB III/41C (boron).

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Fig. 1.

TiB₂. Structure [86I].

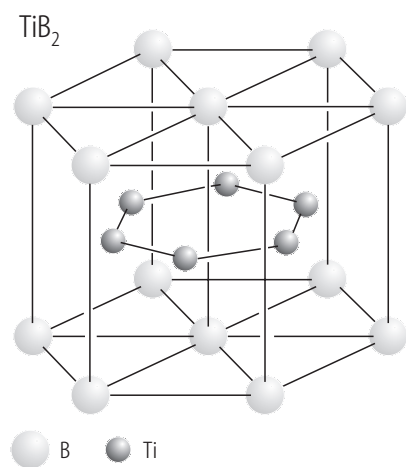


Fig. 2.

TiB₂. Brillouin zone [86I].

TiB₂

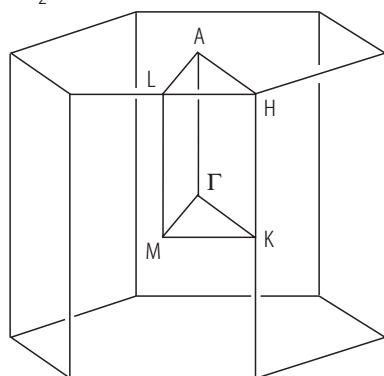


Fig. 3.

ZrB₂. Total and component electronic density of states calculation. The vertical dashed line indicates the position of the Fermi energy [91S].

